



T810H-8F 8A TRIAC

Rev.A.1.1

T810H-8F



JieJie Microelectronics Co., Ltd.

Peak gate current ($t_p=20\mu s$, $T_j=150$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	2.5	kV

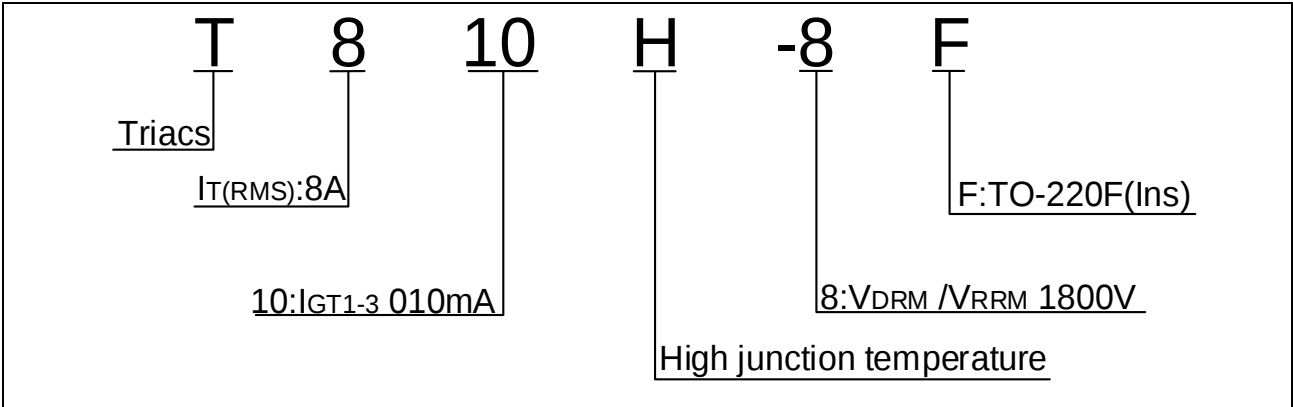




FIG.1: Maximum power dissipation versus RMS on-state current

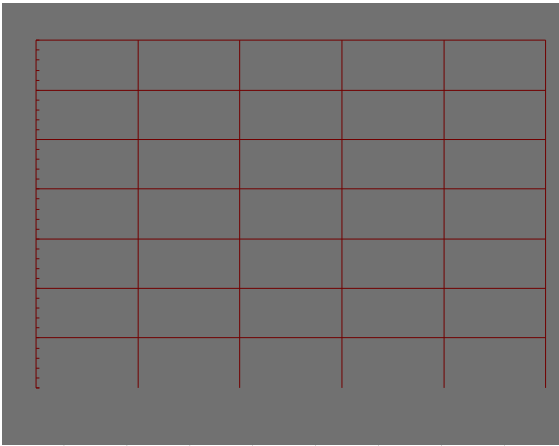
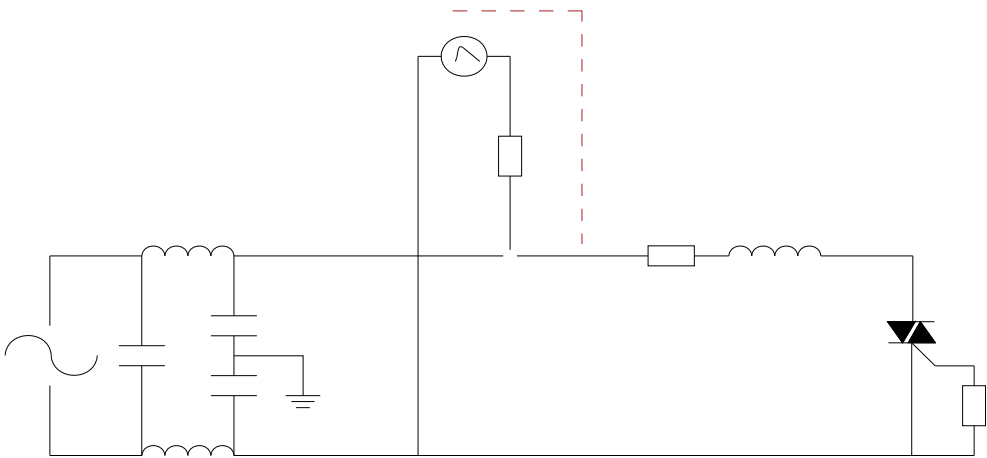


FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards

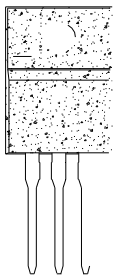




Order code	Voltage V _{DRM} /V _{R_{RRM}} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
T810H-8F	800	10	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
May.19, 2023	A.1.0	Last updated
Oct.10, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA





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